TOSHIBA Transistor Silicon NPN Triple Diffused Type

2SD2406

Power Amplifier Applications

- High power dissipation: $PC = 25 W (Tc = 25^{\circ}C)$
- Good hFE linearity

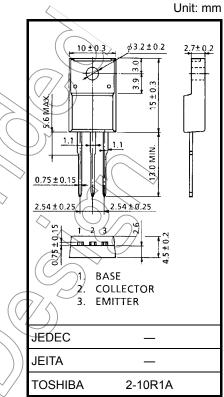
Absolute Maximum Ratings (Tc = 25°C)

| Characteristics | Symbol | Rating | Unit |
|-----------------------------|------------------|------------|------------------------------|
| Collector-base voltage | V _{CBO} | 80 | V |
| Collector-emitter voltage | V _{CEO} | 80 | $(\mathcal{N} \land)$ |
| Emitter-base voltage | V _{EBO} | 5 | $\langle \mathbf{v} \rangle$ |
| Collector current | Ι _C | 4 | Ą |
| Base current | Ι _Β | Q.4 | Ā |
| Collector power dissipation | Pc | 25 | Ŵ |
| (Tc = 25°C) | ГC | | vv |
| Junction temperature | Тј 📿 | 150 | °C |
| Storage temperature range | T _{stg} | -55 to 150 | < °C |

Note: Using continuously under heavy loads (e.g.) the application of high

temperature/current/voltage and the significant change in

temperature, etc.) may cause this product to decrease in the



Weight: 1.7 g (typ.)

reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report

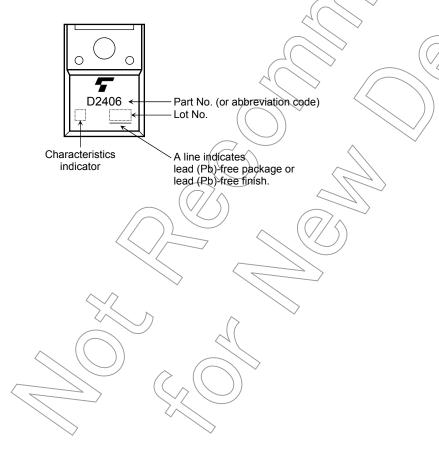
and estimated failure rate, etc).

Electrical Characteristics (Tc = 25°C)

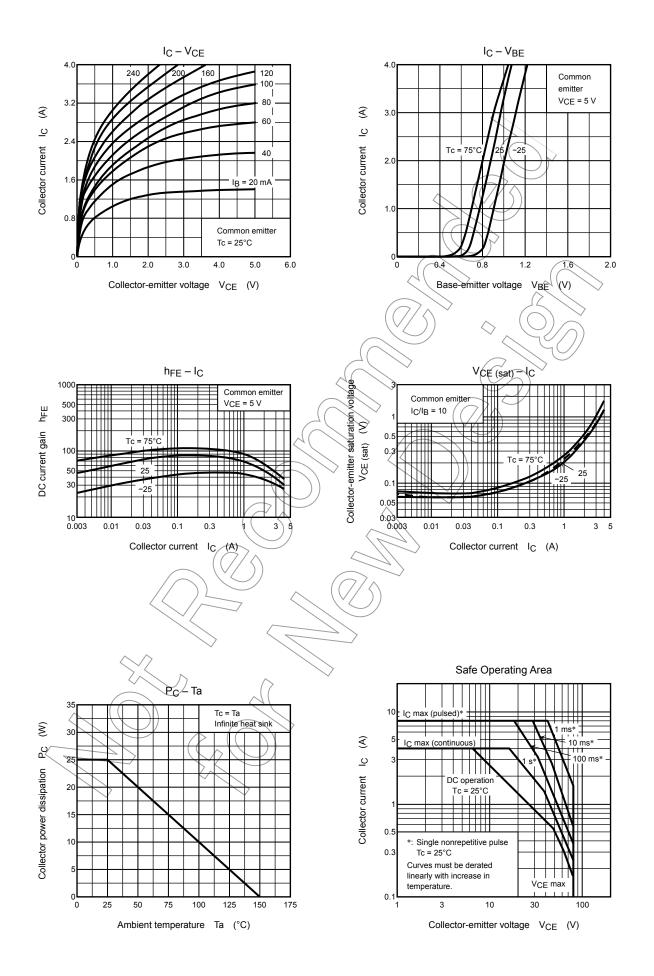
| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------------|-------------------------------|---|-----|------|---------------|------|
| Collector cut-off current | I _{CBO} | V _{CB} = 80 V, I _E = 0 | _ | _ | 30 | μA |
| Emitter cut-off current | I _{EBO} | V _{EB} = 5 V, I _C = 0 | _ | _ | 100 | μA |
| Collector-emitter breakdown voltage | V (BR) CEO | I _C = 50 mA, I _B = 0 | 80 | _ | _ | V |
| Emitter-base breakdown voltage | V (BR) EBO | I _E = 10 mA, I _C = 0 | 5 | | _ | V |
| DC current gain | h _{FE (1)} (Note) | V _{CE} = 5 V, I _C = 0.5 A | 70 | D'- | 240 | |
| | h _{FE (2)} | V _{CE} = 5 V, I _C = 3 A | 15 | 50 | | |
| Collector-emitter saturation voltage | V _{CE (sat)} | I _C = 3 A, I _B = 0.3 A | | 0.45 | 1.5 | V |
| Base-emitter voltage | V _{BE} | V _{CE} = 5 V, I _C = 3 A | _ | 1.0 | 1.5 | V |
| Transition frequency | fT | V _{CE} = 5 V, I _C = 0.5 A | _ | 8.0 | | MHz |
| Collector output capacitance | C _{ob} | V _{CB} = 10 V, I _E = 0, f = 1 MHz | | < 90 | \rightarrow | pF |

Note: hFE (1) classification O: 70 to 140, Y: 120 to 240

Marking



TOSHIBA



RESTRICTIONS ON PRODUCT USE

The information contained herein is subject to change without notice.

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